

### 12V P-Channel Enhancement Mode MOSFET

Voltage

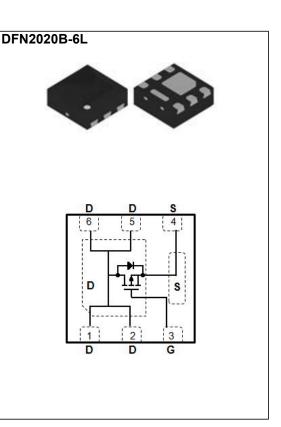
Current

### Features

• RDS(ON), VGS@-4.5V, ID@-6.0A<30mΩ

-12 V

- RDS(ON), VGS@-2.5V, ID@-5.0A<39mΩ
- RDS(ON), VGS@-1.8V, ID@-2.5A<48mΩ
- Advanced Trench Process Technology
- High density cell design for ultra low on-resistance



### **Mechanical Data**

- Case: DFN2020B-6L Package
- Terminals: Solderable per MIL-STD-750, Method 2026

## Maximum Ratings and Thermal Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

-6A

PARAMETER	SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V <sub>DS</sub>	-12	V
Gate-Source Voltage		V <sub>GS</sub>	<u>+</u> 12	V
Continuous Drain Current		Ι <sub>D</sub>	-6	A
Pulsed Drain Current		I <sub>DM</sub>	-24	A
Power Dissipation	T <sub>a</sub> =25°C	PD	2.8	W
	Derate above 25°C		22	mW/ °C
Operating Junction and Storage Temperature Range		T <sub>J</sub> ,T <sub>STG</sub>	-55~150	°C
Typical Thermal Resistance - Junction to Ambient, t<10s <sup>(Note 3)</sup>		R <sub>0JA</sub>	44.6	°C/W



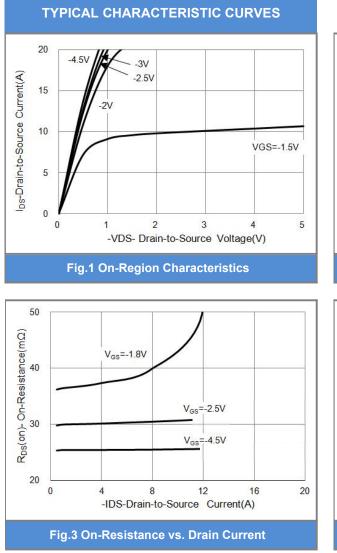
**Electrical Characteristics** (T<sub>A</sub>=25°C unless otherwise noted)

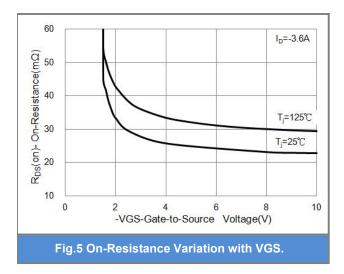
PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static				-		
Drain-Source Breakdown Voltage	$BV_{DSS}$	V <sub>GS</sub> =0V,I <sub>D</sub> =-250uA	-20	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=-250$ uA	-0.35	-0.6	-0.9	V
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =-4.5V,I <sub>D</sub> =-6.0A	-	25	30	mΩ
		V <sub>GS</sub> =-2.5V,I <sub>D</sub> =-5.0A	-	30	39	
		V <sub>GS</sub> =-1.8V,I <sub>D</sub> =-2.5A	-	35	48	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-12V,V <sub>GS</sub> =0V	-	-0.01	-1.0	uA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = <u>+</u> 12V,V <sub>DS</sub> =0V	-	<u>+</u> 10	<u>+</u> 100	nA
Dynamic (Note 6)						
Total Gate Charge	Qg	V <sub>DS</sub> =-10V, I <sub>D</sub> =-7.2A, V <sub>GS</sub> =-4.5V <sup>(Note 1,2)</sup>	-	18.9	-	nC
Gate-Source Charge	$Q_gs$		-	2.8	-	
Gate-Drain Charge	$Q_gd$		-	4.2	-	
Input Capacitance	Ciss		-	1785	-	pF
Output Capacitance	Coss	$V_{DS}$ =-10V, $V_{GS}$ =0V,	-	152	-	
Reverse Transfer Capacitance	Crss	f=1.0MHZ	-	125	-	
Turn-On Delay Time	td <sub>(on)</sub>		-	12	-	
Turn-On Rise Time	tr	$V_{DS}$ =-10V, I <sub>D</sub> =-7.2A, $V_{GEN}$ =-4.5V, R <sub>L</sub> =10Ω $R_{G}$ =6Ω <sup>(Note 1.2)</sup>	-	68	-	ns
Turn-Off Delay Time	td <sub>(off)</sub>		-	82	-	
Turn-Off Fall Time	tf		-	35	-	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	ls		-	-	-1.5	А
Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> =-1A, V <sub>GS</sub> =0V	-	-0.64	-1.2	V

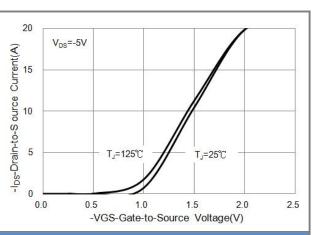
NOTES :

- 1. Pulse width <300us, Duty cycle <2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. The maximum current rating is package limited.
- 4. Repetitive rating, pulse width limited by junction temperature TJ(MAX)=150°C. Ratings are based on low frequency and duty cycles to keep initial TJ=25°C.
- 5.  $R_{\Theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz.square pad of copper.
- 6. Guaranteed by design, not subject to production testing.

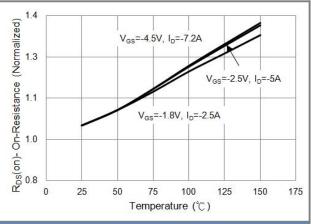




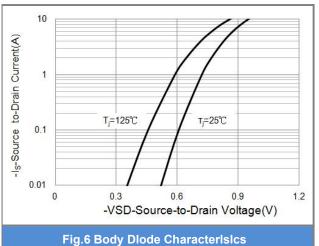




#### **Fig.2 Transfer Characteristics**



#### Fig.4 On-Resistance vs. Junction temperature





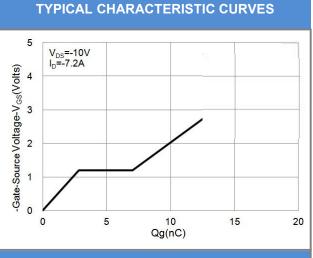


Fig.7 Gate-Charge Characteristics

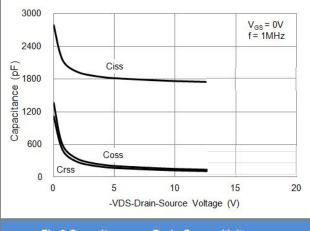
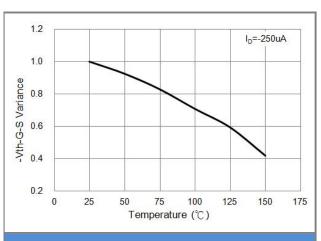


Fig.9 Capacitance vs. Drain-Source Voltage.



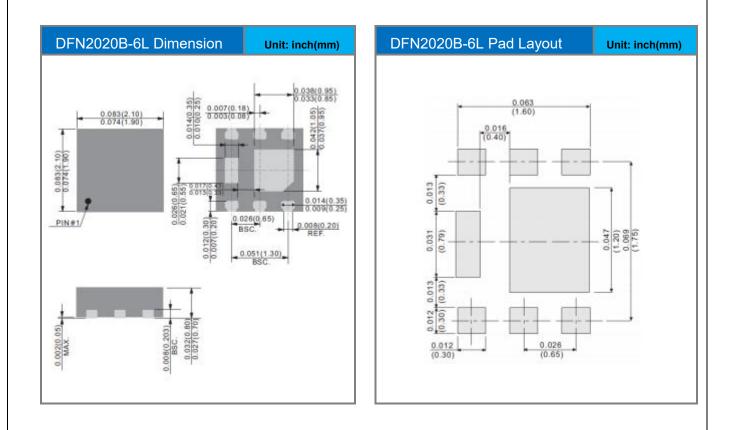




### PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing Type		
CSM112P6D2-2	DFN2020B-6L	3K pcs / 7" reel		

### MOUNTING PAD LAYOUT





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